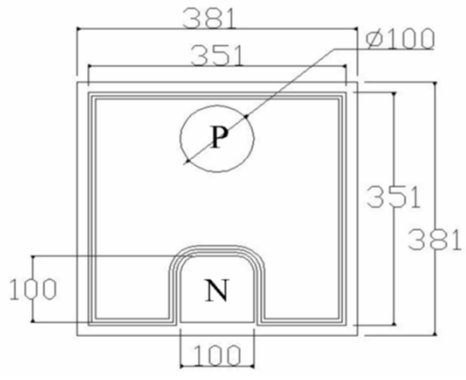
**EPIGAP Optronic GmbH**
Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70
sales@epigap-optronic.de

# Data Sheet

## LED Chip blue-green EOLC-505-34

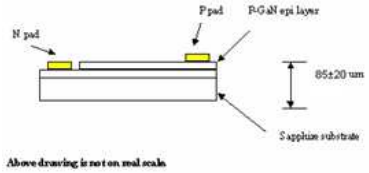
Rev. 03, 2017

| Radiation | Type | Electrodes |
|---|---|---|
| blue-green | GaN / sapphire | P + N up |




Description

- Substrate: sapphire, epitaxial layer: GaN based material
- N bonding pad electrode: Au alloy
- P bonding pad electrode: Au alloy




### Maximum Ratings

$T_{amb}$= 25°C, unless otherwise specified

| Parameter | Test cond. | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Forward current (DC) | | $I_F$ | | | 20 | mA |
| Peak forward current | $t_p \leq$ 50 µs, $t_p/T$=½ | $I_{FM}$ | | | 100 | mA |

### Optical and Electrical Characteristics

$T_{amb}$= 25°C, unless otherwise specified

| Parameter | Test cond. | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Forward voltage | $I_F$=20 mA | $V_F$ | | 3.3 | 3.5 | V |
| Reverse current | $V_R$=5 V | $I_R$ | | | 1 | µA |
| Luminous intensity* | $I_F$=20 mA | $I_v$ | 300 | 400 | 500 | mcd |
| Luminous flux* | $I_F$=20 mA | $\Phi_v$ | | 1700 | | mlm |
| Radiant intensity* | $I_F$=20 mA | $I_e$ | | 1.1 | | mW/sr |
| Radiant power* | $I_F$=20 mA | $\Phi_e$ | | 7.4 | | mW |
| Peak wavelength | $I_F$=20 mA | $\lambda_p$ | | 502 | | nm |
| Dominant wavelength | $I_F$=20 mA | $\lambda_D$ | 502 | 505 | 508 | nm |
| FWHM | $I_F$=20 mA | $\Delta\lambda_{0.5}$ | | 30 | | nm |

*Measured on bare chip on TO-18 header

**Packing:** Chips on adhesive film with wire-bond side top

Art. No. 112 030

RoHS COMPLIANT Pb Pb-Free